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**Oxide-based Materials and Devices
XI**

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IN THIS VOLUME

15 Sessions, 24 Papers, 41 Presentations

Ga2O3: Defects, Doping and Density of States I (3)**Ga2O3: Defects, Doping and Density of States II** (3)**Ga2O3: Material Engineering** (5)**Ga2O3 for Power Applications** (4)**Ga2O3: Applications Driven Material Structuring** (4)**ZnGa2O4 Based Devices and Properties** (5)**Nanostructured Growth, Properties and Applications** (3)**Plasmonics and Photonics** (6)**Electronic Devices** (3)**Photodetectors and Sensors** (1)**Material Properties** (4)**SPIE. PHOTONICS
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Impact of light and ambient gas on the resistance of sputter-deposited non-doped ZnO films ([conference-proceedings-of-spie/11281/112811N/Impact-of-light-and-ambient-gas-on-the-resistance-of/10.1117/12.2550791.full](#))  **Presentation + Paper**
[Yasuhisa Omura](#) ([/profile/Yasuhisa.Omura-4215548](#)); [Shingo Sato](#) ([/profile/Shingo.Sato-4217628](#));

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A systematic study of laser damage threshold for HfO₂, Ta₂O₅, Nb₂O₅, and TiO₂ under manufacturing environments ([conference-proceedings-of-spie/11281/112811O/A-systematic-study-of-laser-damage-threshold-for-HfO2-Ta2O5/10.1117/12.2546519.full](#))  **Presentation + Paper**
[Andrew Gao](#) ([/profile/Andrew.Gao-4210692](#)); [Bojun Zhang](#) ([/profile/notfound?author=Bojun_Zhang](#)); [Evan Yang](#) ([/profile/Yifan.Yang-4216614](#)); [Wenhao Cao](#) ([/profile/Wenhao.Cao-4216628](#));

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Molecular beam epitaxy of Zn-polar ZnO/BeMgZnO heterostructure field effect transistors on GaN and c-sapphire: a comparative study ([conference-proceedings-of-spie/11281/112811Q/Molecular-beam-epitaxy-of-Zn-polar-ZnO-BeMgZnO-heterostructure-field/10.1117/12.2550534.full](#))  **Presentation + Paper**
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Structural and electrical properties of MgO on GaN by thermal atomic layer deposition (Conference Presentation) ([conference-proceedings-of-spie/11281/112811R/Structural-and-electrical-properties-of-MgO-on-GaN-by-thermal/10.1117/12.2548753.full](#))  **Presentation Only**
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Electronic coupling in ZnO asymmetric quantum wells for intersubband cascade devices ([conference-proceedings-of-spie/11281/112811S/Electronic-coupling-in-ZnO-asymmetric-quantum-wells-for-intersubband-cascade/10.1117/12.2547478.full](#)) 
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